

## KSE13009F

### **High Voltage Switch Mode Application**

- High Speed Switching
- Suitable for Switching Regulator and Motor Control



### **NPN Silicon Transistor**

### Absolute Maximum Ratings T<sub>C</sub>=25°C unless otherwise noted

| Symbol           | Parameter                                    | Value     | Units<br>V |  |
|------------------|--|-----------|------------|--|
| V <sub>CBO</sub> | Collector-Base Voltage                       | 700       |            |  |
| V <sub>CEO</sub> | Collector-Emitter Voltage                    | 400       | V          |  |
| V <sub>EBO</sub> | Emitter-Base Voltage                         | 9         | V          |  |
| I <sub>C</sub>   | Collector Current (DC)                       | 12        | А          |  |
| I <sub>CP</sub>  | Collector Current (Pulse)                    | 24        | Α          |  |
| I <sub>B</sub>   | Base Current                                 | 6         | Α          |  |
| P <sub>C</sub>   | Collector Dissipation (T <sub>C</sub> =25°C) | 50        | W          |  |
| T <sub>J</sub>   | Junction Temperature                         | 150       | °C         |  |
| T <sub>STG</sub> | Storage Temperature                          | -65 ~ 150 | °C         |  |

### Electrical Characteristics T<sub>C</sub>=25°C unless otherwise noted

| Symbol                 | Parameter                            | Test Condition                | Min. | Тур.  | Max. | Units |
|------------------------|--------------------------------------|-------------------------------|------|-------|------|-------|
| V <sub>CEO</sub> (sus) | Collector-Emitter Sustaining Voltage | $I_C = 10 \text{mA}, I_B = 0$ | 400  |       |      | V     |
| I <sub>EBO</sub>       | Emitter Cut-off Current              | $V_{EB} = 7V, I_{C} = 0$      |      |       | 1    | mA    |
| h <sub>FE</sub>        | DC Current Gain                      | $V_{CE} = 5V, I_{C} = 5A$     | 8    |       | 40   |       |
|                        |                                      | $V_{CE} = 5V, I_{C} = 8A$     | 6    |       | 30   |       |
| V <sub>CE</sub> (sat)  | Collector-Emitter Saturation Voltage | $I_C = 5A, I_B = 1A$          |      |       | 1    | V     |
|                        |                                      | $I_C = 8A, I_B = 1.6A$        | 197  | _ = 7 | 1.5  | V     |
|                        |                                      | $I_C = 12A, I_B = 3A$         | - 1  | 0.73  | 3    | V     |
| V <sub>BE</sub> (sat)  | Base-Emitter Saturation Voltage      | $I_C = 5A, I_B = 1A$          |      | . W.Y | 1.2  | V     |
|                        |                                      | $I_C = 8A, I_B = 1.6A$        |      |       | 1.6  | V     |
| C <sub>ob</sub>        | Output Capacitance                   | $V_{CB} = 10V$ , $f = 0.1MHz$ |      | 180   |      | pF    |
| f <sub>T</sub>         | Current Gain Bandwidth Product       | $V_{CE} = 10V, I_{C} = 0.5A$  | 4    |       |      | MHz   |
| t <sub>ON</sub>        | Turn ON Time                         | $V_{CC} = 125V, I_{C} = 8A$   |      |       | 1.1  | μs    |
| t <sub>STG</sub>       | Storage Time                         | $I_{B1} = -I_{B2} = 1.6A$     |      |       | 3    | μs    |
| t <sub>F</sub>         | Fall Time                            | $R_L = 15,6\Omega$            |      |       | 0.7  | μs    |

\* Pulse Test: PW≤300μs, Duty Cycle≤2%

## **Typical Characteristics**

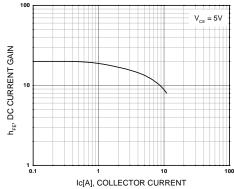


Figure 1. DC current Gain



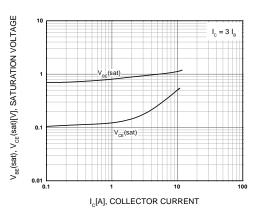


Figure 2. Base-Emitter Saturation Voltage **Collector-Emitter Saturation Voltage** 

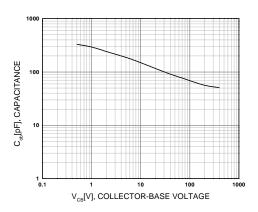


Figure 3. Collector Output Capacitance

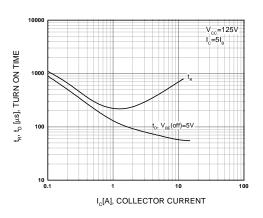


Figure 4. Turn On Time

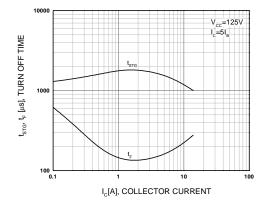


Figure 5. Turn Off Time

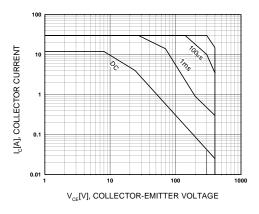


Figure 6. Safe Operating Area

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# Typical Characteristics (Continued)

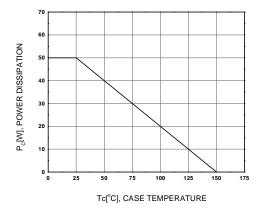
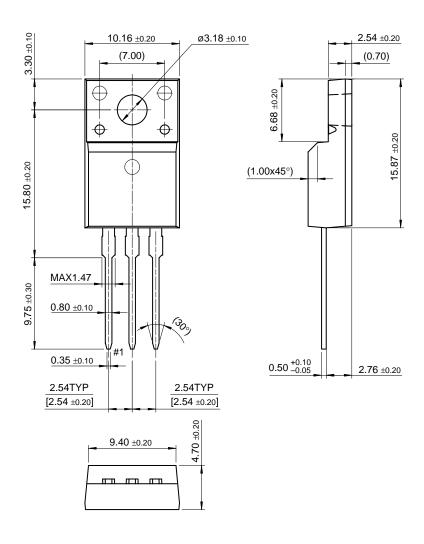


Figure 1. DC current Gain

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## **Package Demensions**

## TO-220F



Dimensions in Millimeters

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